## **1.8 Volt Rail-to-Rail Operational Amplifier**

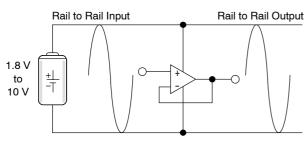
The NCS7101 operational amplifier provides rail-to-rail operation on both the input and output. The output can swing within 50 mV of each rail. This rail-to-rail operation enables the user to make full use of the entire supply voltage range available. It is designed to work at very low supply voltages (1.8 V and ground), yet can operate with a supply of up to 10 V and ground. The NCS7101 is available in the space saving SOT-23-5 package with two industry standard pinouts.

### **Features**

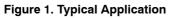
- Low Voltage, Single Supply Operation (1.8 V and Ground to 10 V and Ground)
- 1.0 pA Input Bias Current
- Unity Gain Bandwidth of 1.0 MHz at 5.0 V, 0.9 MHz at 1.8 V
- Output Voltage Swings Within 50 mV of Both Rails @ 1.8 V
- No Phase Reversal on the Output for Over-Driven Input Signals
- Input Offset Trimmed to 1.0 mV
- Low Supply Current ( $I_D = 1.0 \text{ mA}$ )
- Works Down to Two Discharged NiCd Battery Cells
- ESD Protected Inputs Up to 2.0 kV
- These Devices are Pb-Free and are RoHS Compliant
- AEC-Q100 Qualified and PPAP Capable
- \*NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements

### **Typical Applications**

- Dual NiCd/NiMH Cell Powered Systems
- Portable Communication Devices
- Low Voltage Active Filters
- Power Supply Monitor and Control
- Interface to DSP



This device contains 68 active transistors.





### **ON Semiconductor®**

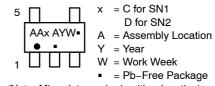
http://onsemi.com

### LOW VOLTAGE **RAIL-TO-RAIL OPERATIONAL AMPLIFIER**

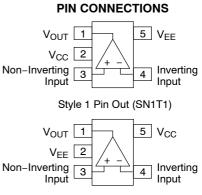


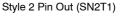
### SOT-23-5 **SN SUFFIX**

### MARKING DIAGRAM



(Note: Microdot may be in either location)





### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NCS7101SN1T1G		
NCV7101SN1T1G*		
	SOT-23-5	3000 Tape & Reel
NCS7101SN2T1G	(Pb-Free)	(7 inch Reel)
NCV7101SN2T1G*	r.	

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Supply Voltage (V <sub>CC</sub> to V <sub>EE</sub> )	V <sub>S</sub>	10	V
Input Differential Voltage Range (Note 1)	V <sub>IDR</sub>	V <sub>EE</sub> – 300 mV to 10 V	V
Input Common Mode Voltage Range (Note 1)	V <sub>ICR</sub>	V <sub>EE</sub> – 300 mV to 10 V	V
Output Short Circuit Duration (Note 2)	t <sub>SC</sub>	Indefinite	sec
Junction Temperature	TJ	150	°C
Power Dissipation and Thermal Characteristics – SOT-23-5 Package Thermal Resistance, Junction-to-Air Power Dissipation @ $T_A = 70^{\circ}C$	R <sub>θJA</sub> P <sub>D</sub>	220 364	°C/W mW
Storage Temperature Range	T <sub>stg</sub>	–65 to +150	°C
Operating Ambient Temperature Range NCS7101 NCV7101	T <sub>A</sub>	-40 to +85 -40 to +125	°C
ESD Protection at any Pin Human Body Model (Note 3)	V <sub>ESD</sub>	2000	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Either or both inputs should not exceed the range of V<sub>EE</sub> - 300 mV to V<sub>EE</sub> + 10 V.
Maximum package power dissipation limits must be observed to ensure that the maximum junction temperature is not exceeded.

 $T_{J} = T_{A} + (P_{D}R_{\theta JA})$ 3. ESD data available upon request.

### DC ELECTRICAL CHARACTERISTICS

(V\_{CC} = 2.5 V, V\_{EE} = –2.5 V, V\_{CM} = V\_O = 0, RL to GND, TA = 25°C, unless otherwise noted.)

Characteristics	Symbol	Min	Тур	Max	Unit
Input Offset Voltage	V <sub>IO</sub>				mV
$V_{CC} = 0.9 \text{ V}, \text{ V}_{EE} = -0.9 \text{ V}$					
$T_A = 25^{\circ}C$ $T_A = T_A$ to $T_{AB}$		-7.0 -9.0	0.6	7.0 9.0	
$T_A = T_{Low}$ to $T_{High}$ V <sub>CC</sub> = 2.5 V, V <sub>EE</sub> = -2.5 V		-9.0	_	9.0	
$T_{A} = 25^{\circ}C$		-7.0	0.6	7.0	
$T_A = T_{Low}$ to $T_{High}$		-9.0	-	9.0	
$V_{CC} = 5.0 \text{ V}, V_{EE} = -5.0 \text{ V}$					
$T_A = 25^{\circ}C$		-7.0	0.6	7.0	
$T_A = T_{Low}$ to $T_{High}$		-9.0	-	9.0	
Input Offset Voltage Temperature Coefficient ( $R_S = 50$ ) $T_A = -40^{\circ}C$ to $125^{\circ}C$	$\Delta V_{IO} / \Delta T$	-	8.0	-	μV/°C
Input Bias Current (V <sub>CC</sub> = 1.8 V to 10 V)	I <sub>IB</sub>	-	1.0	-	pА
Common Mode Input Voltage Range	V <sub>ICR</sub>	V <sub>EE</sub>	-	V <sub>CC</sub>	V
Large Signal Voltage Gain	A <sub>VOL</sub>				kV/V
$V_{CC} = 5.0 \text{ V}, \text{ V}_{EE} = -5.0 \text{ V}$					
$R_L = 10 k\Omega$		16	50	-	
$R_L = 2.0 \text{ k}\Omega$		16	30	-	
Output Voltage Swing, High ( $V_{ID} = \pm 0.2 V$ )	V <sub>OH</sub>				V
$V_{CC} = 0.9 \text{ V}, V_{EE} = -0.9 \text{ V} (T_A = 25^{\circ}\text{C})$ $R_L = 10 \text{ k}$		0.85	0.88	_	
$R_{\rm L} = 2.0  \rm k$		0.80	0.82	_	
$T_A = T_{Low}$ to $T_{High}$					
$R_L = 10 k$		0.85	-	-	
$R_{L} = 2.0 k$		0.79	-	-	
$V_{CC} = 2.5 \text{ V}, V_{EE} = -2.5 \text{ V} (T_A = 25^{\circ}\text{C})$ $R_I = 600$		2.10	2.21		
$R_{\rm L} = 2.0  \rm k$		2.10	2.44	_	
$T_A = T_{Low}$ to $T_{High}$		2.00			
$R_L = 600$		2.00	-	-	
R <sub>L</sub> = 2.0 k		2.40	-	-	
$V_{CC} = 5.0 \text{ V}, V_{EE} = -5.0 \text{ V} (T_A = 25^{\circ}\text{C})$					
$R_{L} = 600$ $R_{L} = 2.0 \text{ k}$		4.40 4.80	4.60 4.88	-	
$T_A = T_{Low}$ to $T_{High}$		4.00	4.00	_	
$R_L = 600$		4.40	-	-	
$R_{L} = 2.0 \text{ k}$		4.80	-	-	
Output Voltage Swing, Low ( $V_{ID} = \pm 0.2 V$ )	V <sub>OL</sub>				V
$V_{CC} = 0.9 \text{ V}, V_{EE} = -0.9 \text{ V} (T_A = 25^{\circ}\text{C})$	02				
R <sub>L</sub> = 10 k		-	-0.88	-0.85	
$R_{L} = 2.0 \text{ k}$		-	-0.82	-0.80	
$T_A = T_{Low}$ to $T_{High}$				0.95	
R <sub>L</sub> = 10 k R <sub>L</sub> = 2.0 k		_	_	-0.85 -0.78	
$V_{CC} = 2.5 \text{ V}, V_{EE} = -2.5 \text{ V} (T_A = 25^{\circ}\text{C})$				0.70	
$R_L = 600$		-	-2.22	-2.10	
$R_{L} = 2.0 \text{ k}$		-	-2.38	-2.35	
$T_A = T_{Low}$ to $T_{High}$				0.00	
R <sub>L</sub> = 600 R <sub>L</sub> = 2.0 k		-	-	-2.00 -2.30	
$H_L = 2.0 \text{ k}$ $V_{CC} = 5.0 \text{ V}, \text{ V}_{EE} = -5.0 \text{ V} (T_A = 25^{\circ}\text{C})$		- I		-2.30	
$R_{\rm L} = 600$		-	-4.66	-4.40	
$R_{L}$ = 2.0 k		-	-4.88	-4.80	
$T_A = T_{Low}$ to $T_{High}$					
R <sub>L</sub> = 600		-	-	-4.35	
R <sub>L</sub> = 2.0 k		-	-	-4.80	
Common Mode Rejection Ratio	CMRR				dB
$V_{in} = 0$ to 10 V		65	-	-	
V <sub>in</sub> = 0 to 5.0 V		60	-	-	

### DC ELECTRICAL CHARACTERISTICS (continued)

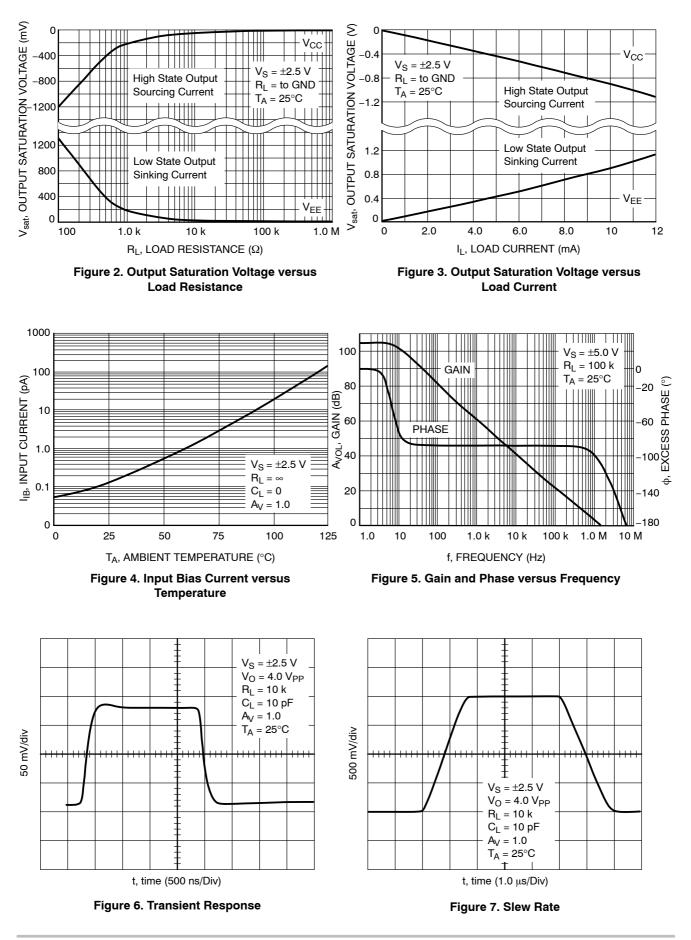
(V\_{CC} = 2.5 V, V\_{EE} = -2.5 V, V\_{CM} = V\_O = 0, R\_L to GND, T\_A = 25^{\circ}C, unless otherwise noted.)

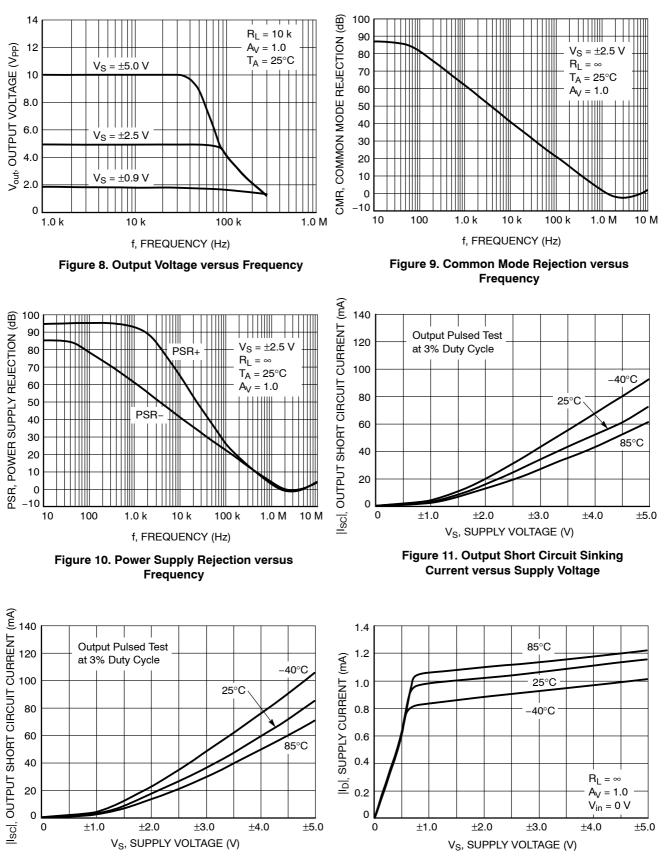
Characteristics	Symbo	ol Min	Тур	Max	Unit
Power Supply Rejection Ratio $V_{CC}/V_{EE} = 10 V/Ground, \Delta V_{S} = 2.5 V$	PSRF	8 65	_	_	dB
Output Short Circuit Current ( $V_{in}$ Diff = ± 1.0 V)	I <sub>SC</sub>				mA
$V_{CC} = +0.9 \text{ V}, \text{ V}_{EE} = -0.9 \text{ V}$					
Source		-	3.0	-	
Sink		-	-3.0	-	
$V_{CC}$ = +2.5 V, $V_{EE}$ = -2.5 V					
Source		20	25	60	
Sink		-60	-25	-20	
$V_{CC} = 5.0 \text{ V}, V_{EE} = -5.0 \text{ V}$					
Source		50	72	140	
Sink		-140	-72	-50	
Power Supply Current (V <sub>O</sub> = 0 V)	ا <sub>D</sub>				mA
$V_{CC} = +0.9 \text{ V}, V_{EE} = -0.9 \text{ V}$					
$T_A = 25^{\circ}C$		-	0.97	1.20	
$T_A = -40^{\circ}C$ to $85^{\circ}C$		-	-	1.30	
$T_A = -40^{\circ}C$ to 125°C		-	-	1.60	
V <sub>CC</sub> = +2.5 V, V <sub>EE</sub> = -2.5 V					
$T_A = 25^{\circ}C$		-	1.05	1.30	
$T_A = -40^{\circ}C$ to $85^{\circ}C$		-	-	1.40	
$T_{A} = -40^{\circ}C \text{ to } 125^{\circ}C$		-	-	1.70	
$V_{CC} = 5.0 \text{ V}, V_{EE} = -5.0 \text{ V}$					
$T_A = 25^{\circ}C$		-	1.13	1.40	
$T_{A} = -40^{\circ}C \text{ to } 85^{\circ}C$		-	-	1.50	
$T_A = -40^{\circ}C$ to $125^{\circ}C$		-	-	1.80	

### AC ELECTRICAL CHARACTERISTICS

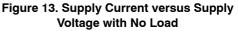
 $(V_{CC} = 2.5 \text{ V}, V_{EE} = -2.5 \text{ V}, V_{CM} = V_O = 0, R_L \text{ to GND}, T_A = 25^{\circ}\text{C}, \text{ unless otherwise noted.})$ 

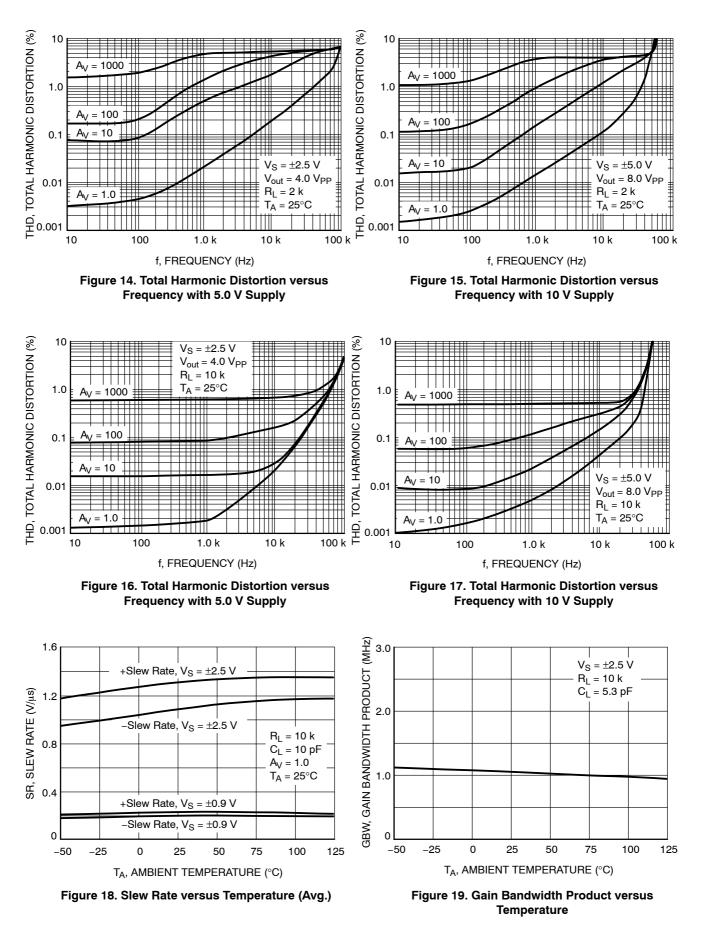
Characteristics	Symbol	Min	Тур	Max	Unit
Slew Rate (V_O = -2.0 to 2.0 V, R_L = 2.0 k\Omega, A_V = 1.0)	SR	0.7	1.2	3.0	V/μs
Gain Bandwidth Product (V <sub>CC</sub> = 10 V)	GBW	0.5	1.0	3.0	MHz
Gain Margin (R <sub>L</sub> = 10 k, C <sub>L</sub> = 5.0 pF)	Am	-	6.5	-	dB
Phase Margin (R <sub>L</sub> = 10 k, C <sub>L</sub> = 5.0 pF)	φm	-	60	-	Deg
Power Bandwidth (V_O = 4.0 Vpp, R_L = 2.0 k\Omega, THD $\leq$ 1.0%)	BW <sub>P</sub>	-	130	-	kHz
Total Harmonic Distortion (V <sub>O</sub> = 4.0 Vpp, R <sub>L</sub> = 2.0 kΩ, A <sub>V</sub> = 1.0) f = 1.0 kHz f = 10 kHz	THD		0.02 0.2	- -	%
Differential Input Resistance (V <sub>CM</sub> = 0 V)	R <sub>in</sub>	-	>1.0	-	tera $\Omega$
Differential Input Capacitance (V <sub>CM</sub> = 0 V)	C <sub>in</sub>	-	2.0	-	pF
Equivalent Input Noise Voltage (Freq = 1.0 kHz)	e <sub>n</sub>	-	140	-	nV/√Hz

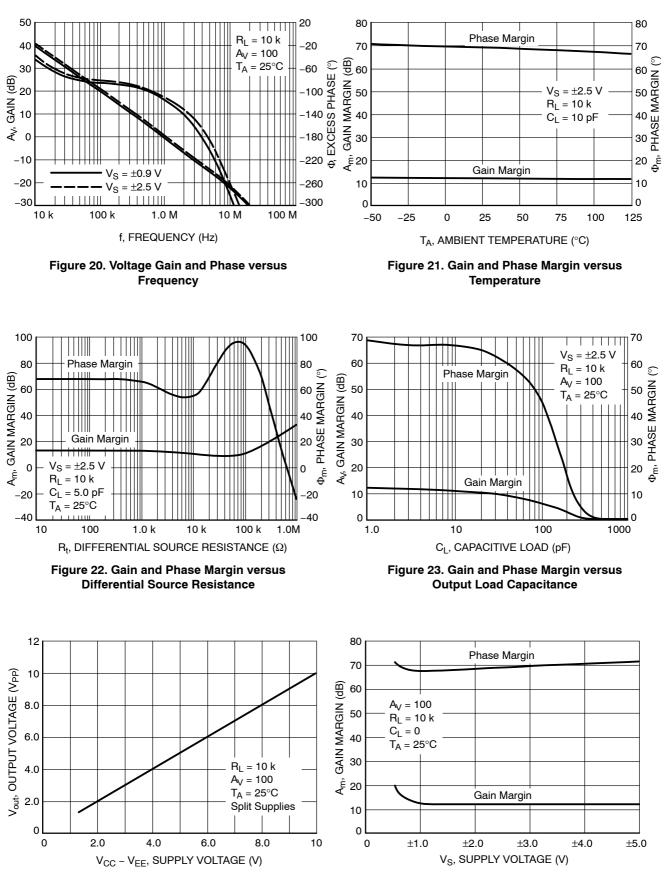


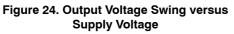


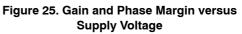


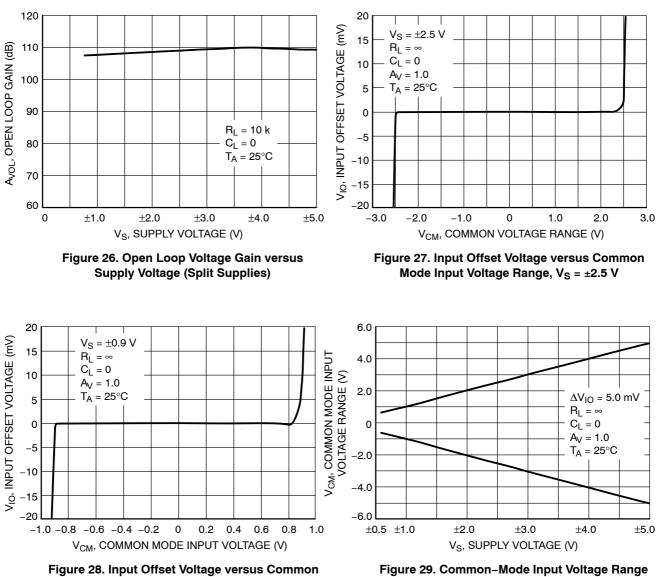












Mode Input Voltage Range,  $V_S = \pm 0.9 V$ 

Figure 29. Common–Mode Input Voltage Range versus Power Supply Voltage

#### APPLICATION INFORMATION AND OPERATING DESCRIPTION

#### **GENERAL INFORMATION**

The NCS7101 is a rail-to-rail input, rail-to-rail output operational amplifier that features guaranteed 1.8 volt operation. This feature is achieved with the use of a modified analog CMOS process that allows the implementation of depletion MOSFET devices. The amplifier has a 1.0 MHz gain bandwidth product, 1.2 V/ $\mu$ s slew rate and is operational over a power supply range less than 1.8 V to as high as 10 V.

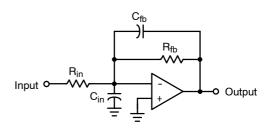
#### Inputs

The input topology of this device series is unconventional when compared to most low voltage operational amplifiers. It consists of an N-channel depletion mode differential transistor pair that drives a folded cascode stage and current mirror. This configuration extends the input common mode voltage range to encompass the V<sub>EE</sub> and V<sub>CC</sub> power supply rails, even when powered from a combined total of less than 1.8 volts. Figures 27 and 28 show the input common mode voltage range versus power supply voltage.

The differential input stage is laser trimmed in order to minimize offset voltage. The N-channel depletion mode MOSFET input stage exhibits an extremely low input bias current of less than 40 pA. The input bias current versus temperature is shown in Figure 4. Either one or both inputs can be biased as low as  $V_{EE}$  minus 300 mV to as high as 10 V without causing damage to the device. If the input common mode voltage range is exceeded, the output will not display a phase reversal but it may latch in the appropriate high or low state. The device can then be reset by removing and reapplying power. If the maximum input positive or negative voltage ratings are to be exceeded, a series resistor must be used to limit the input current to less than 2.0 mA.

The ultra low input bias current of the NCS7101 allows the use of extremely high value source and feedback resistor without reducing the amplifier's gain accuracy. These high value resistors, in conjunction with the device input and printed circuit board parasitic capacitances  $C_{in}$ , will add an additional pole to the single pole amplifier shown in Figure 30. If low enough in frequency, this additional pole can reduce the phase margin and significantly increase the output settling time. The effects of  $C_{in}$ , can be canceled by placing a zero into the feedback loop. This is accomplished with the addition of capacitor  $C_{fb}$ . An approximate value for  $C_{fb}$  can be calculated by:

$$C_{\text{fb}} = \frac{R_{\text{in}} \times C_{\text{in}}}{R_{\text{fb}}}$$



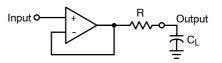
Cin = Input and printed circuit board capacitance

Figure 30. Input Capacitance Pole Cancellation

#### Output

The output stage consists of complementary P and N channel devices connected to provide rail-to-rail output drive. With a 2.0 k load, the output can swing within 100 mV of either rail. It is also capable of supplying over 95 mA when powered from 10 V and 3.0 mA when powered from 1.8 V.

When connected as a unity gain follower, the NCS7101 can directly drive capacitive loads in excess of 390 pF at room temperature without oscillating but with significantly reduced phase margin. The unity gain follower configuration exhibits the highest bandwidth and is most prone to oscillations when driving a high value capacitive load. The capacitive load in combination with the amplifier's output impedance, creates a phase lag that can result in an under-damped pulse response or a continuous oscillation. Figure 32 shows the effect of driving a large capacitive load in a voltage follower type of setup. When driving capacitive loads exceeding 390 pF, it is recommended to place a low value isolation resistor between the output of the op amp and the load, as shown in Figure 31. The series resistor isolates the capacitive load from the output and enhances the phase margin. Refer to Figure 33. Larger values of R will result in a cleaner output waveform but excessively large values will degrade the large signal rise and fall time and reduce the output's amplitude. Depending upon the capacitor characteristics, the isolation resistor value will typically be between 50 to 500 ohms. The output drive capability for resistive and capacitive loads is shown in Figures 2, 3, and 23.



Isolation resistor R = 50 to 500

Figure 31. Capacitance Load Isolation

Note that the lowest phase margin is observed at cold temperature and low supply voltage.

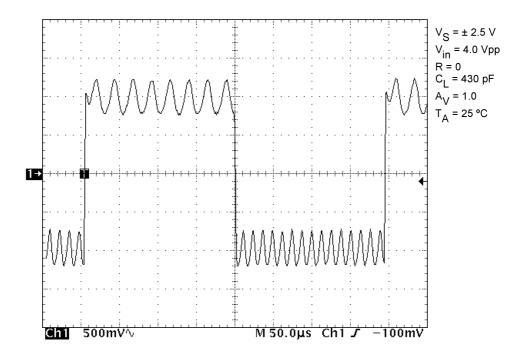


Figure 32. Small Signal Transient Response with Large Capacitive Load

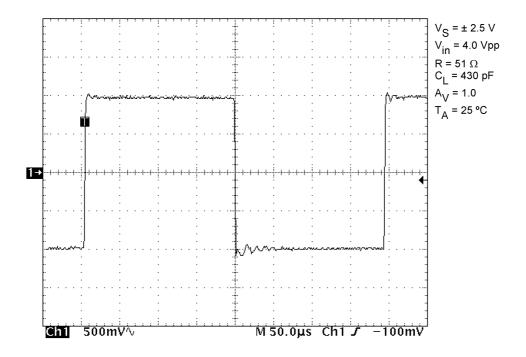
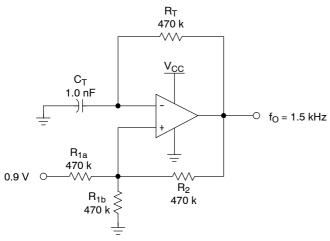
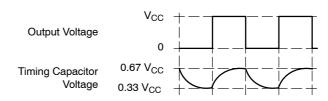


Figure 33. Small Signal Transient Response with Large Capacitive Load and Isolation Resistor.

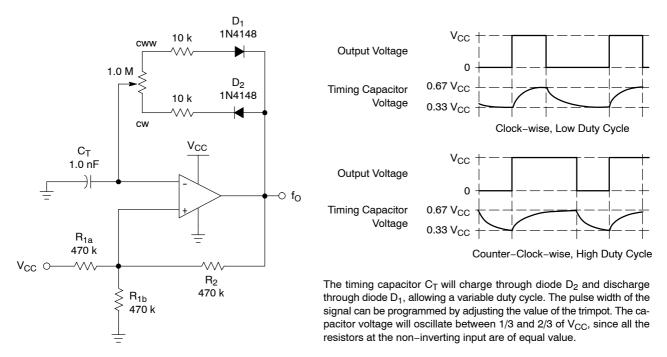


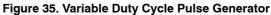


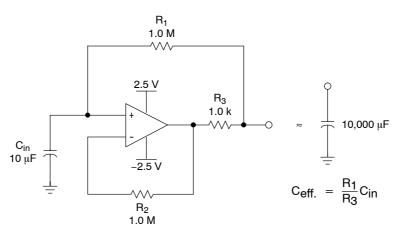
The non–inverting input threshold levels are set so that the capacitor voltage oscillates between 1/3 and 2/3 of V<sub>CC</sub>. This requires the resistors R<sub>1a</sub>, R<sub>1b</sub> and R<sub>2</sub> to be of equal value. The following formula can be used to approximate the output frequency.

$$f_{O} = \frac{1}{1.39 \ R_{T}C_{T}}$$

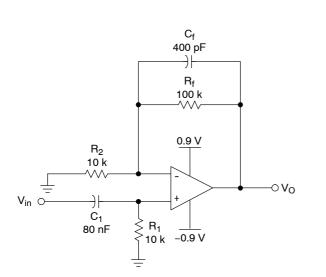


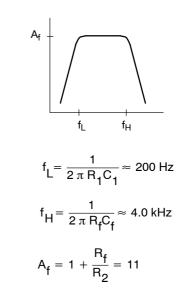




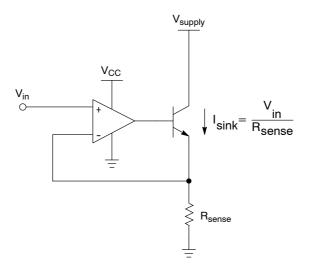




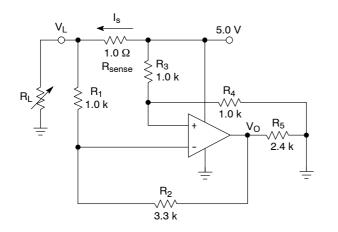












I <sub>s</sub>	vo
1.00 A	67.93 mV
0.50 A	78.67 mV

For best performance, use low tolerance resistors.

Figure 39. High Side Current Sense

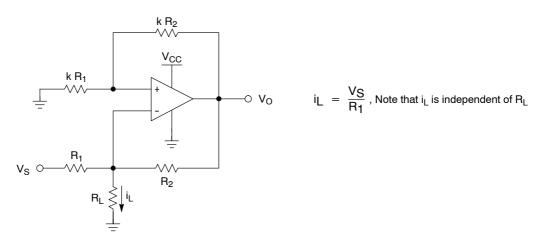


Figure 40. Current Source

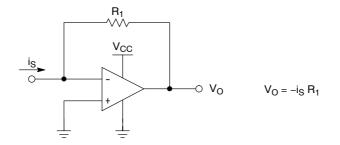
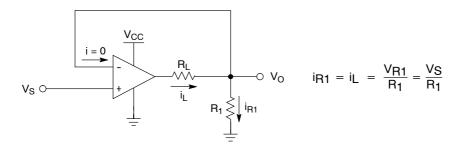
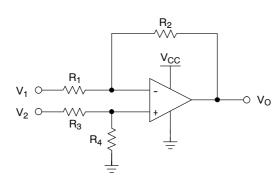
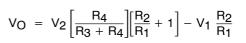


Figure 41. Current to Voltage Converter



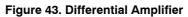


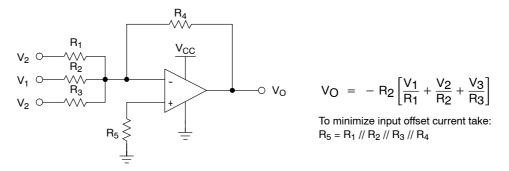




If  $R_1 = R_3$ , and  $R_2 = R_4$ , the equation simplifies to:

$$V_{O} = (V_{2} - V_{1}) \ \frac{R_{2}}{R_{1}}$$

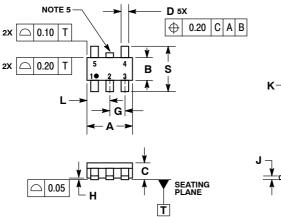






### PACKAGE DIMENSIONS

TSOP-5 CASE 483-02 ISSUE H





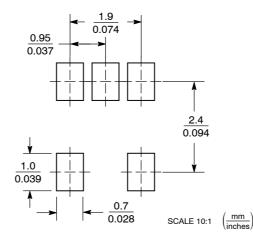


NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M. 1994.
- ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: MILLIMETERS. 3. MAXIMU LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS, MINIMUM LEAD THIOLOGO ID TUCKNESS, MINIMUM LEAD THIOLOGO ID TUCKNESS, MINIMUM LEAD
- THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL. 4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE
- BURRS. 5. OPTIONAL CONSTRUCTION: AN ADDITIONAL TRIMMED LEAD IS ALLOWED IN THIS LOCATION. TRIMMED LEAD NOT TO EXTEND MORE THAN 0.2 FROM BODY.

	MILLIMETERS			
DIM	MIN MAX			
Α	3.00 BSC			
В	1.50	BSC		
С	0.90	1.10		
D	0.25	0.50		
G	0.95 BSC			
н	0.01	0.10		
J	0.10	0.26		
к	0.20	0.60		
L	1.25	1.55		
м	0 °	10 °		
s	2.50	3.00		

#### SOLDERING FOOTPRINT\*



\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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